

	L #	Hits	Search Text	DBs	Time Stamp
1	L1	211	438/406.ccls.	USPAT; EPO; JPO	2001/04/19 17:55
2	L5	748	438/455-459.ccls.	USPAT; EPO; JPO	2001/04/19 17:55
3	L9	819	1 5	USPAT; EPO; JPO	2001/04/19 18:05
4	L13	338	9 and (soi or ((silicon semiconductor) adj (insulator sapphire)))	USPAT; EPO; JPO	2001/04/19 18:07
5	L17	314	9 and (soi or ((silicon semiconductor) adj (insulating)))	USPAT; EPO; JPO	2001/04/19 18:07
6	L21	342	13 17	USPAT; EPO; JPO	2001/04/19 18:36
7	L25	18925	interconnect\$3 near10 (insulat\$3 dielectric oxide)	USPAT; EPO; JPO	2001/04/19 18:51
8	L29	74	9 and 25	USPAT; EPO; JPO	2001/04/19 18:38
9	L33	9	9 and (buried embedded) near3 interconnect\$3	USPAT; EPO; JPO	2001/04/19 18:52

	L #	Hits	Search Text	DBs	Time Stamp
1	L1	748	438/455-459.ccls.	USPAT; EPO; JPO	2001/04/19 14:09
2	L5	211	438/406.ccls.	USPAT; EPO; JPO	2001/04/19 14:09
3	L9	819	1 5	USPAT; EPO; JPO	2001/04/19 14:10
4	L13	1673	interconnect near5 dielectric	USPAT; EPO; JPO	2001/04/19 14:10
5	L17	9	9 and 13	USPAT; EPO; JPO	2001/04/19 14:10